

AMENDMENT TO THE ABSTRACT:

1. Please amend the Abstract as follows. Applicant attaches to this paper a clean version of the amended Abstract, labeled "Replacement Abstract."

~~A semiconductor device comprises a convex semiconductor layer provided on a semiconductor substrate, a source region and a drain region provided in the convex semiconductor layer, and a gate electrode. The gate electrode has a side wall gate portion provided over a side surface of the convex semiconductor layer in an insulated state with respect to the convex semiconductor layer.~~ A semiconductor device includes a semiconductor substrate of a first conductivity type, a convex semiconductor layer of the first conductivity type on the semiconductor substrate, a source region and a drain region of a second conductivity type in the convex semiconductor layer, a gate insulator on side surfaces of the convex semiconductor layer and a top surface of the convex semiconductor layer, a gate electrode on a portion of the gate insulator between the source region and the drain region, and a trench capacitor. The trench capacitor is provided in the semiconductor substrate and is connected to one of the source and drain regions.